

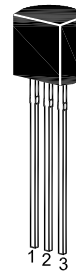
2SB564

PNP Silicon Epitaxial Planar Transistor

for use in driver and output stages of audio frequency amplifiers.

The transistor is subdivided into three groups O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	30	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	25	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	1	A
Power Dissipation	P_{tot}	800	mW
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{\text{CE}} = 1\text{ V}$, $-I_{\text{C}} = 100\text{ mA}$ Current Gain Group	O				
	Y				
	G				
	h_{FE}	70	-	140	-
	h_{FE}	120	-	240	-
	h_{FE}	200	-	400	-
Collector Base Cutoff Current at $-V_{\text{CB}} = 30\text{ V}$	$-I_{\text{CBO}}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_{\text{C}} = 100\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{CBO}}$	30	-	-	V
Collector Emitter Breakdown Voltage at $-I_{\text{C}} = 10\text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	25	-	-	V
Emitter Base Breakdown Voltage at $-I_{\text{E}} = 100\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{EBO}}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_{\text{C}} = 1\text{ A}$, $-I_{\text{B}} = 100\text{ mA}$	$-V_{\text{CE(sat)}}$	-	-	0.5	V
Base Emitter Saturation Voltage at $-I_{\text{C}} = 1\text{ A}$, $-I_{\text{B}} = 100\text{ mA}$	$-V_{\text{BE(sat)}}$	-	-	1.2	V
Gain Bandwidth Product at $-V_{\text{CE}} = 6\text{ V}$, $-I_{\text{E}} = 10\text{ mA}$	f_{T}	-	110	-	MHz
Collector Base Capacitance at $-V_{\text{CB}} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	18	-	pF

